Resolution Plot

DESIGN MSX25-1000

Wafer No.: **3145-6**

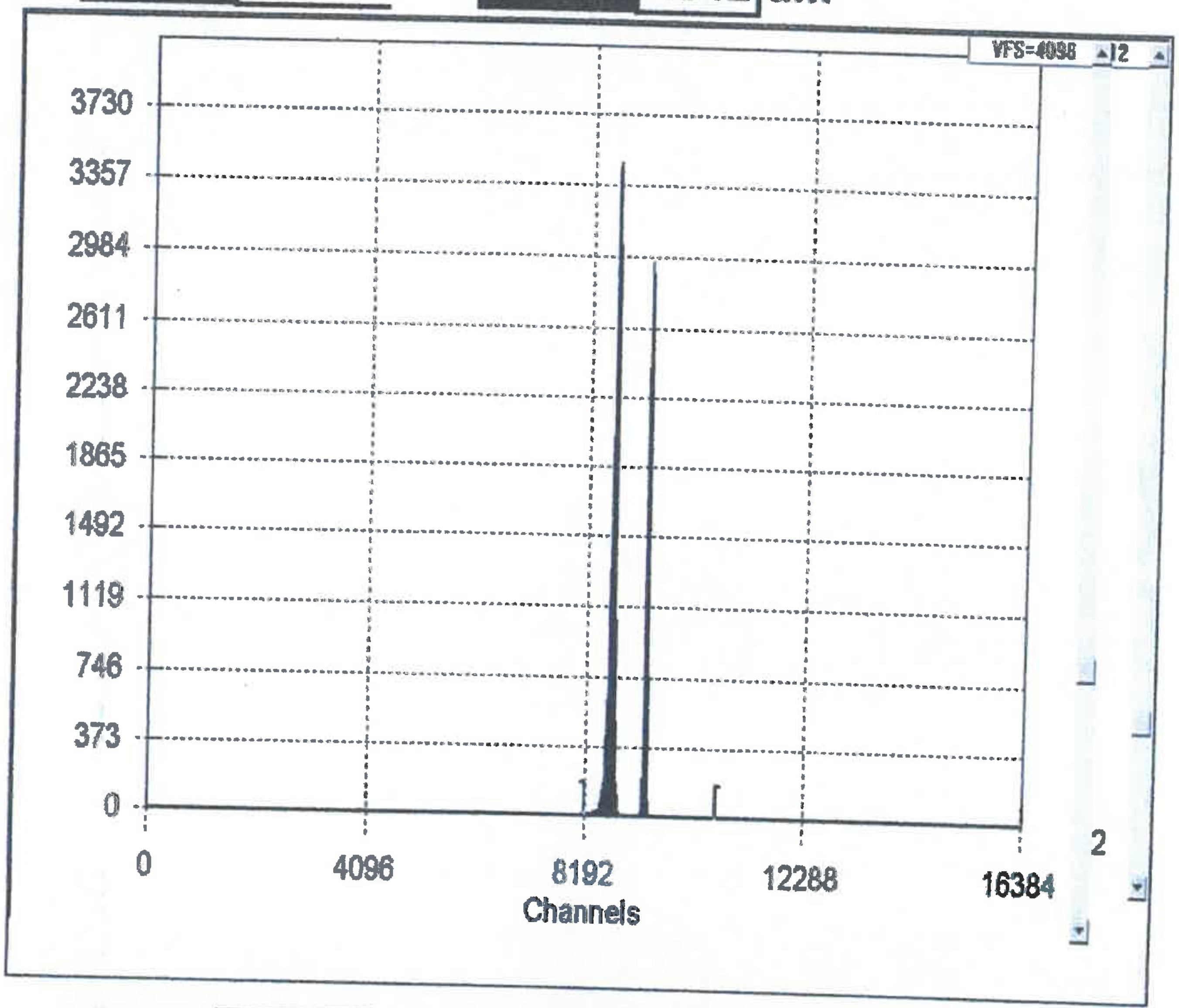
Thickness: **1042** um

JUNCTION

DET LINE:	45.2	KeV
SYSTEM:	28.1	KeV
CAL:	35.4	KeV

OHMIC

DET LINE:	46.9	KeV
SYSTEM:	28.3	KeV
CALC:	37.4	KeV



Source: Am 241

Rise Time: 1

Flat Top: 0

BIAS VOLTS= 110 V

Leakage 214 nA

Micron Semiconductor
18/11/2014

CUSTOMER: STOCK
PURCHASE ORDER NUMBER:
DEVICE TYPE: MSX25-1000
DATE: 13/11/2014

MEASUREMENT DATA IN AIR:

TEMPERATURE: 22°c
HUMIDITY: 42%

DEVICE NUMBER	THICKNESS	OPERATING VOLTAGE (V)	IR @ DEP.	IR @ DEP.+30V	VB @ 10uA	VF @ 10mA
3145-6	1042uM	80	208	216	>200	0.58